

Notice of References Cited

Application/Control No.

09/536,087

Applicant(s)/Patent Under
Reexamination
Li et al.

Examiner

Toniae M Thomas

Art Unit

2822

Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification	
*	A	US-4,702,936-B1	10-1987	Maeda et al.	427	583
*	B	US-4,863,755-B1	09-1989	Hess et al.	427	574
*	C	US-5,234,869-B1	08-1993	Mikata et al.	438	793
*	D	US-5,302,366-B1	04-1994	Schuetz et al.	423	346
*	E	US-5,591,494-B1	01-1997	Sato et al.	427	579
*	F	US-5,968,611-B1	10-1999	Kaloyeros et al.	427	579
*	G	US-6,159,871-B1	12-2000	Loboda et al.	438	786
	H	US- -				
	I	US- -				
	J	US- -				
	K	US- -				
	L	US- -				
	M	US- -				

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification	
	N	EP-0464515-	01-1992	EP	Mikata et al.	H01L	21/318
	O	EP-0771886-	05-1997	EP	Loboda	C23C	16/36
	P	- -					
	Q	- -					
	R	- -					
	S	- -					
	T	- -					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)					
	U	Loboda et al., "Using Trimethylsilane to Improve Safety, Throughput and Versatility in PECVD Processes", Electrochemical Proceedings, vol. 97-10, pages 443-453. <i>Cited in Paper # 13</i>					
	V	Laxman et al., "Synthesizing Low k CVD materials for Fab Use", Semiconductor International (Nov 2000), pages 95-102. <i>Cited in Paper # 13</i>					
	W	Anonymous, "New Gas Helps Make Faster ICs", Machine Design, (Nov 4, 1999), page 118. <i>Cited in Paper # 13</i>					
	X						

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.